

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	19464	groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:12
S2	1159	etch\$3 near groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:42
S3	4727	etch\$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:42
S4	346	wet adj etch\$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:44
S5	559	wet adj etch\$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:46
S6	175	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:43
S7	26	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and foreign	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:48
S8	28	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and particles	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:47

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S9	1	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and round with corners	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:48
S10	4	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and round\$3 with corner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:48
S11	1	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and rounding with corner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:45
S12	4	wet adj etch\$3 with groove and wafer and semiconductor and spin\$4 and rounding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:47
S13	23	support with substrate and wet adj etch\$3 with groove and wafer and semiconductor and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52
S14	41	support with substrate and wet with etch\$3 with groove and wafer and semiconductor and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:48
S15	74	support with substrate and wet with etch\$3 same groove and wafer and semiconductor and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:48
S16	1	support with substrate and wet adj etch\$3 with groove and wafer and semiconductor and rounding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52

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S17	23	support with substrate and wet adj etch\$3 with groove and wafer and semiconductor and round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52
S18	5963	groove same etch\$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:22
S19	1159	groove near etch\$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:22
S20	25	groove near etch\$3 same round\$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:41
S21	3	groove near etch\$3 same round\$3 and wafer and semiconductor and support\$3 with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:30
S22	10	groove near etch\$3 same round\$3 and wafer and semiconductor and wet with etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:32
S23	1	groove near wet near etch\$3 same round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:42
S24	7	trench near wet near etch\$3 same round\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:44

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S25	0	trench near wet near etch\$3 same round\$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:45
S26	6	trench with wet near etch\$3 same round\$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:53
S27	7	(trench or groove) with wet near etch\$3 same round\$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:54
S28	4	(trench or groove) and wet near etch\$3 with round\$3 and support with substrate and damage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:56
S29	82	wet near etch\$3 with round\$3 and damage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:57
S30	92	wet near etch\$3 with round\$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:02
S31	63	wet near etch\$3 with round\$3 and spin\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:03
S32	1	wet near etch\$3 with round\$3 and spin\$4 same revers\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:03

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S33	186	wet near etch\$3 and spin\$4 same revers\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:04
S34	104	wet near etch\$3 and spin\$4 same revers\$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:04
S35	1	wet near etch\$3 and spin\$4 same revers\$3 and damage with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:05
S36	6	wet near etch\$3 and spin\$4 same revers\$3 and residue with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08
S37	10	wet with etch\$3 and spin\$4 same revers\$3 and residue with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08
S38	153	wet with etch\$3 and spin\$4 same revers\$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08
S39	3	wet with etch\$3 and spin\$4 near revers\$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:10
S40	1	wet with etch\$3 same spin\$4 near revers\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:54

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S41	1207	(438/745).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:55
S42	206	(438/747).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:55
S43	244	microbalance and heater	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:12
S44	77	microbalance and heater and organic and detection	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:15
S45	63	microbalance and heater and organic and detection and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:15